

Silicon NPN Power Transistors

2SD362

DESCRIPTION

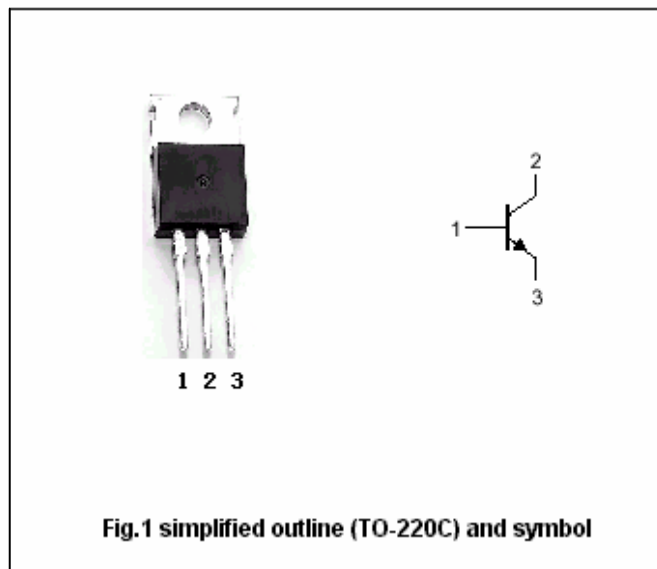
- With TO-220C package
- Collector-base voltage: $V_{CBO}=150V$
- Collector current : $I_C=5A$
- Collector dissipation : $P_C=40$ ($T_C=25^\circ$)

APPLICATIONS

- For B/W TV horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_a=25^\circ$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	150	V
V_{CEO}	Collector-emitter voltage	Open base	70	V
V_{EBO}	Emitter-base voltage	Open collector	8	V
I_C	Collector current (DC)		5	A
P_C	Collector dissipation	$T_C=25^\circ$	40	W
T_j	Junction temperature		150	$^\circ$
T_{stg}	Storage temperature		-55~150	$^\circ$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=1mA; I_E=0$	150			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=2mA; R_{BE}=\infty$	70			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA; I_C=0$	8			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=5A; I_B=0.5A$			1.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=5A; I_B=0.5A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=100V; I_E=0$			20	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V; I_C=0$			20	μA
h_{FE}	DC current gain	$I_C=5A; V_{CE}=5V$	20		140	
f_T	Transition frequency	$I_C=0.5A; V_{CE}=5V$		10		MHz

◆ h_{FE} classifications

N	R	O
20-50	40-80	70-140

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PACKAGE OUTLINE

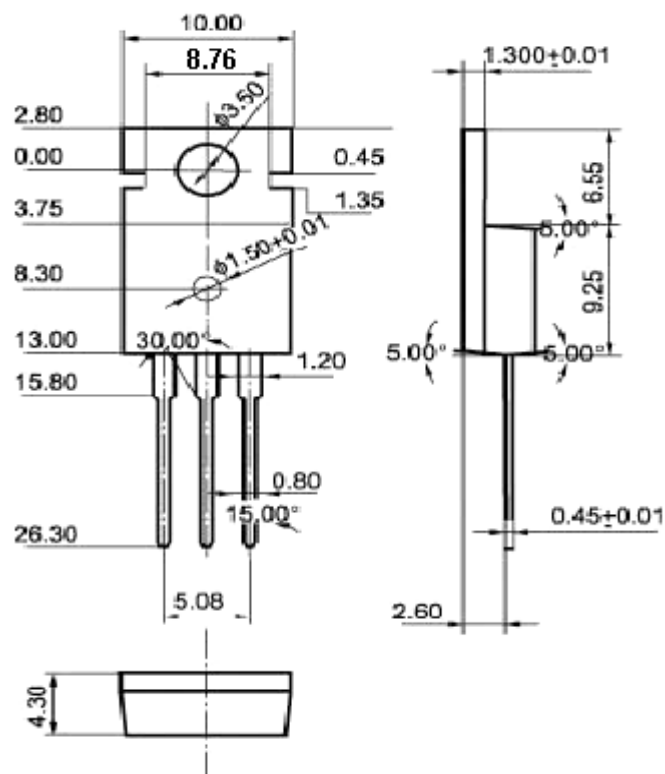


Fig.2 Outline dimensions (unindicated tolerance:±0.10mm)

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